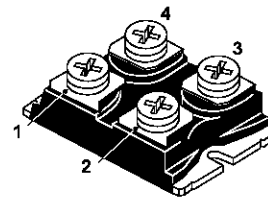


NPN TRANSISTOR POWER MODULE

- EASY TO DRIVE TECHNOLOGY (ETD)
- HIGH CURRENT POWER BIPOLAR MODULE
- VERY LOW R_{th} JUNCTION CASE
- SPECIFIED ACCIDENTAL OVERLOAD AREAS
- ISOLATED CASE (2500V RMS)
- EASY TO MOUNT
- LOW INTERNAL PARASITIC INDUCTANCE

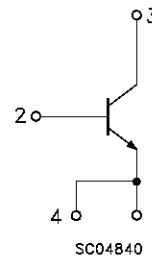
APPLICATIONS:

- MOTOR CONTROL
- SMPS & UPS
- WELDING EQUIPMENT



ISOTOP

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage ($V_{BE} = -5\text{ V}$)	1000	V
$V_{CEO(sus)}$	Collector-Emitter Voltage ($I_B = 0$)	450	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	80	A
I_{CM}	Collector Peak Current ($t_p = 10\text{ ms}$)	160	A
I_B	Base Current	18	A
I_{BM}	Base Peak Current ($t_p = 10\text{ ms}$)	27	A
P_{tot}	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	270	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max Operation Junction Temperature	150	$^\circ\text{C}$
V_{iso}	Insulation Withstand Voltage (AC-RMS)	2500	V

THERMAL DATA

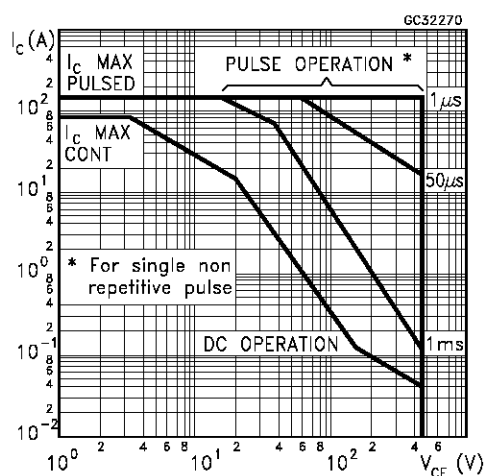
$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.41	$^{\circ}C/W$
R_{thc-h}	Thermal Resistance Case-heatsink With Conductive Grease Applied	Max	0.05	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

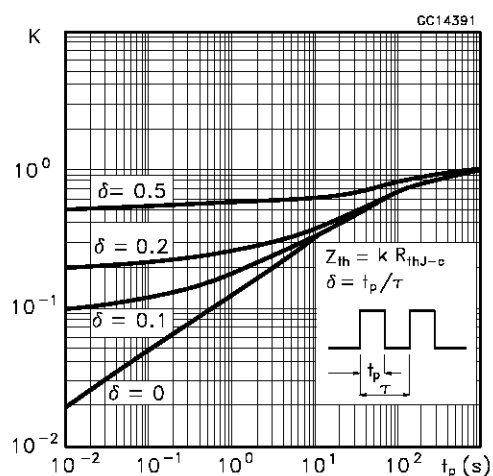
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CER}	Collector Cut-off Current ($R_{BE} = 5 \Omega$)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ $T_j = 100^{\circ}C$			0.2 2	mA mA
I_{CEV}	Collector Cut-off Current ($V_{BE} = -1.5V$)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ $T_j = 100^{\circ}C$			0.2 2	mA mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5 V$			1	mA
$V_{CEO(SUS)}^*$	Collector-Emitter Sustaining Voltage	$I_C = 0.2 A$ $L = 25 mH$ $V_{clamp} = 450 V$	450			V
h_{FE}^*	DC Current Gain	$I_C = 60 A$ $V_{CE} = 5 V$		15		
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 30 A$ $I_B = 3 A$ $I_C = 30 A$ $I_B = 3 A$ $T_j = 100^{\circ}C$ $I_C = 60 A$ $I_B = 12 A$ $I_C = 60 A$ $I_B = 12 A$ $T_j = 100^{\circ}C$		0.35 0.5	2 2	V V V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 60 A$ $I_B = 12 A$ $I_C = 60 A$ $I_B = 12 A$ $T_j = 100^{\circ}C$		1.1	1.5	V V
di_C/dt	Rate of Rise of On-state Collector	$V_{CC} = 300 V$ $R_C = 0$ $t_p = 3 \mu s$ $I_{B1} = 18 A$ $T_j = 100^{\circ}C$	150			A/ μs
$V_{CE(3 \mu s)}$	Collector-Emitter Dynamic Voltage	$V_{CC} = 300 V$ $R_C = 30 \Omega$ $I_{B1} = 18 A$ $T_j = 100^{\circ}C$		4	6	V
$V_{CE(5 \mu s)}$	Collector-Emitter Dynamic Voltage	$V_{CC} = 300 V$ $R_C = 30 \Omega$ $I_{B1} = 18 A$ $T_j = 100^{\circ}C$		2	3	V
t_s t_f t_c	Storage Time Fall Time Cross-over Time	$I_C = 30 A$ $V_{CC} = 50 V$ $V_{BB} = -5 V$ $R_{BB} = 0.2 \Omega$ $V_{clamp} = 400 V$ $I_{B1} = 3 A$ $L = 25 \mu H$ $T_j = 100^{\circ}C$		4.5 0.1 0.3	5 0.2 5	μs μs μs
V_{CEW}	Maximum Collector Emitter Voltage Without Snubber	$I_{CWOFF} = 80 A$ $I_{B1} = 16 A$ $V_{BB} = -5 V$ $V_{CC} = 50 V$ $L = 80 \mu H$ $R_{BB} = 0.2 \Omega$ $T_j = 125^{\circ}C$	400			V

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

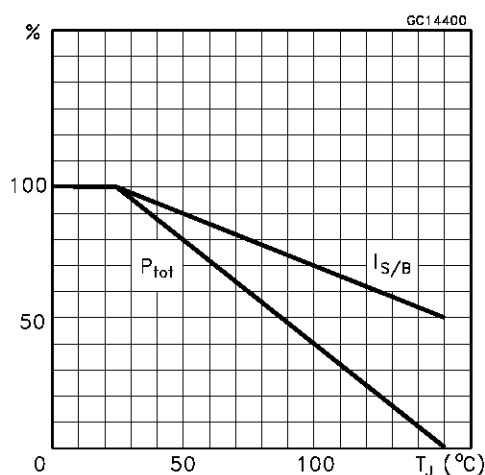
Safe Operating Areas



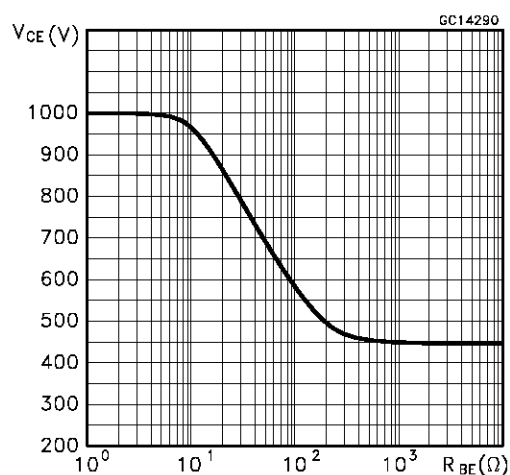
Thermal Impedance



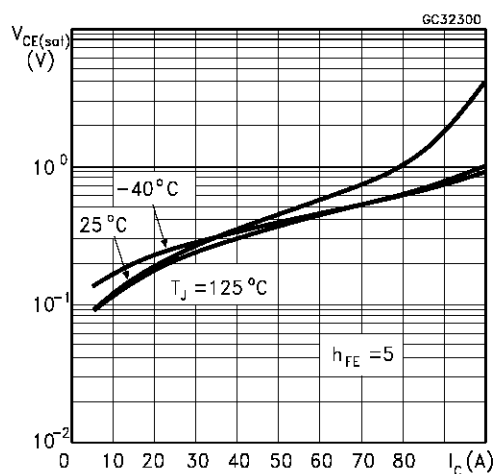
Derating Curve



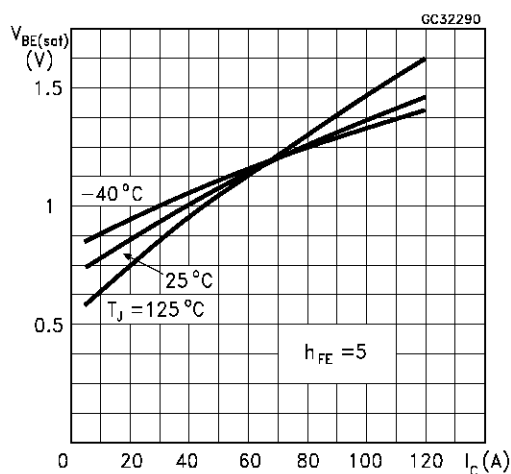
Collector-Emitter Voltage Versus Base-Emitter Resistance



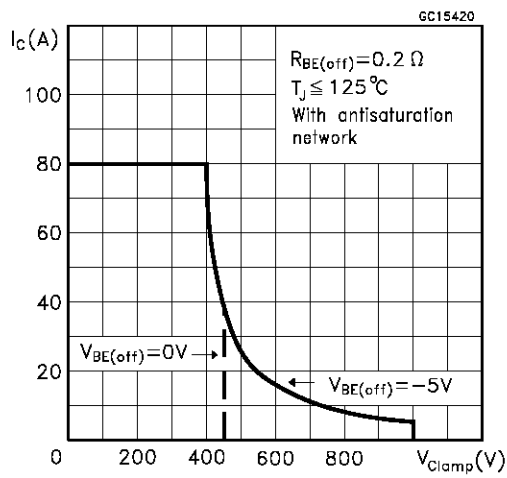
Collector-Emitter Saturation Voltage



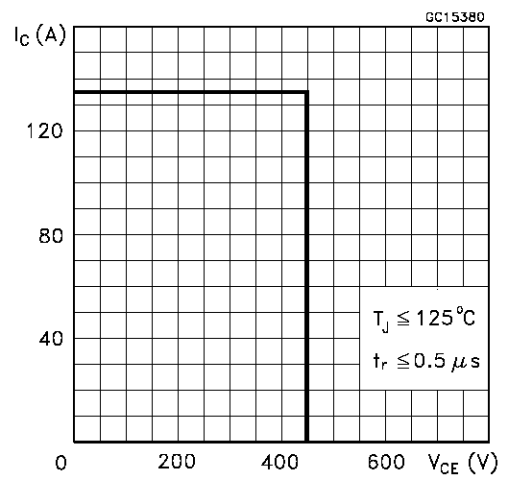
Base-Emitter Saturation Voltage



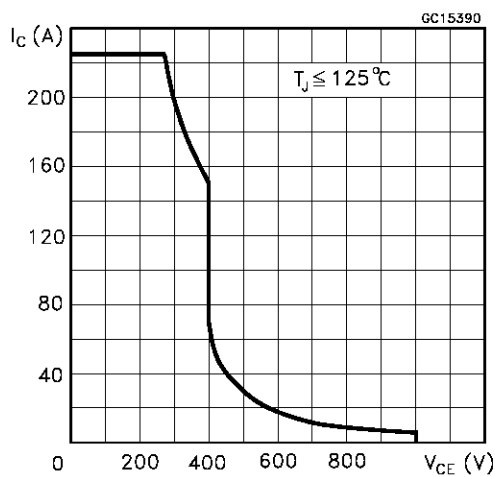
Reverse Biased SOA



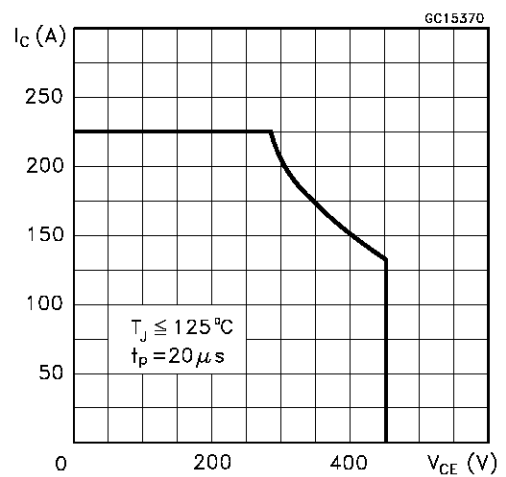
Forward Biased SOA



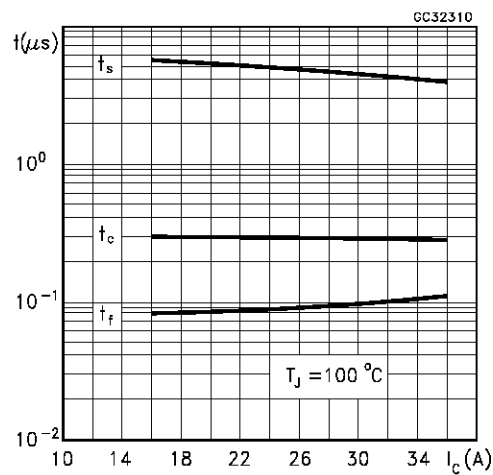
Reverse Biased SOA



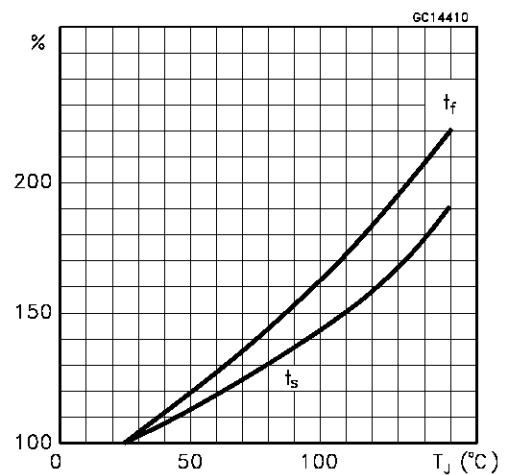
Forward Biased SOA



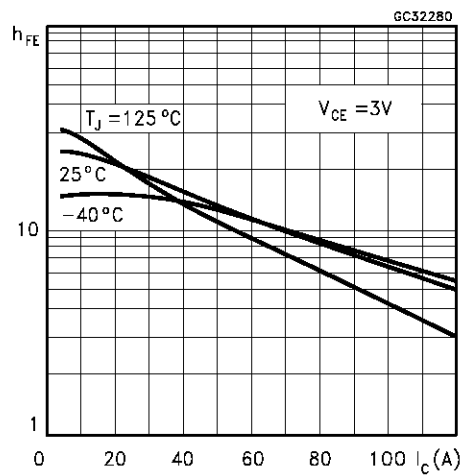
Switching Time Inductive Load



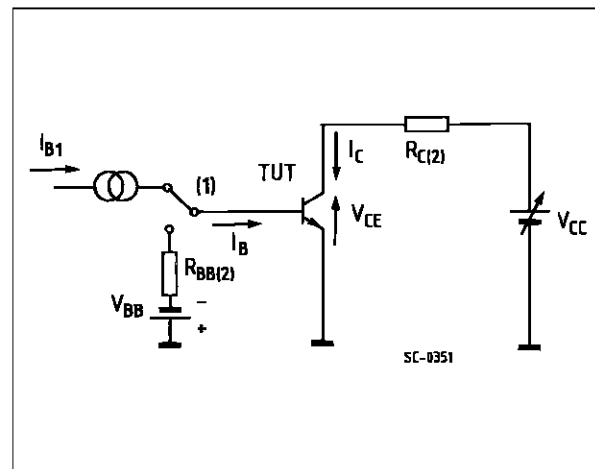
Switching Time Inductive Load Versus Temperature



DC Current Gain



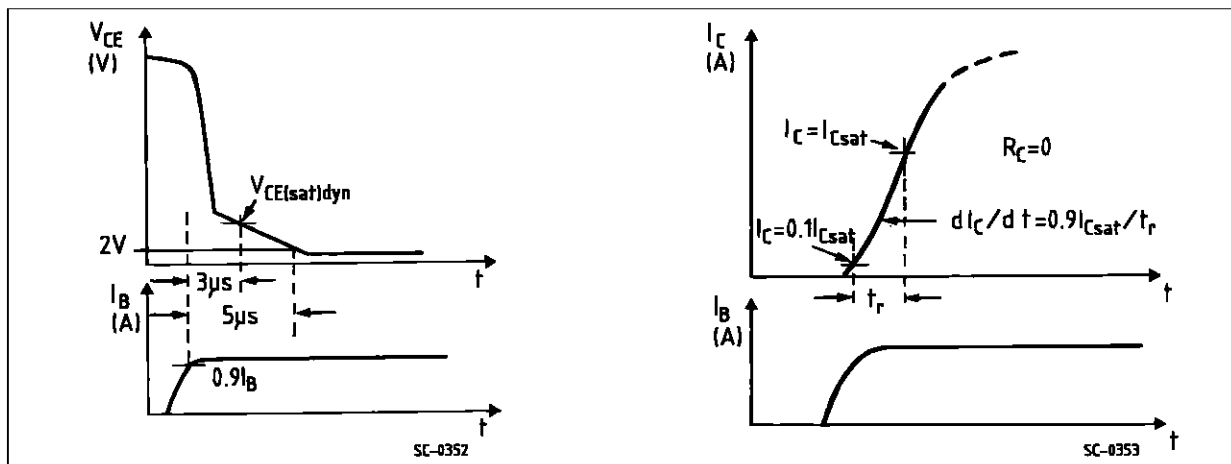
Turn-off Switching Test Circuit



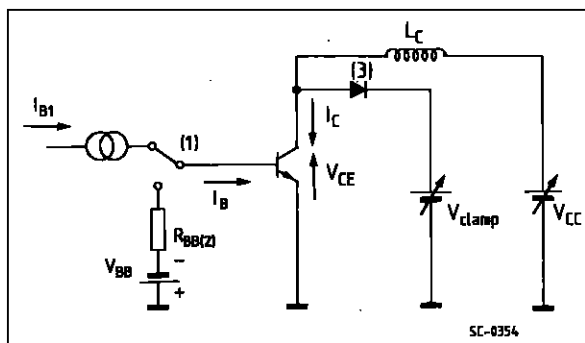
1) Fast electronic switch

2) Non-inductive Resistor

Turn-on Switching Waveforms.



Turn-off Switching Test Circuit

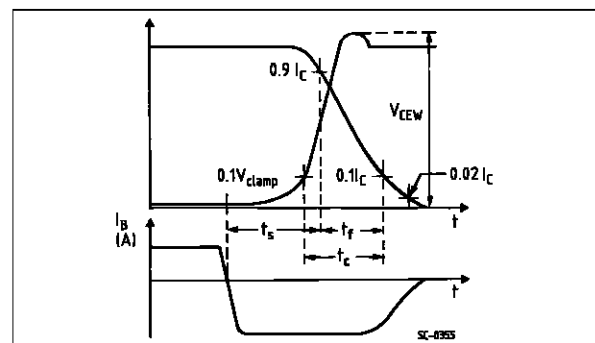


1) Fast electronic switch

2) Non-inductive Resistor

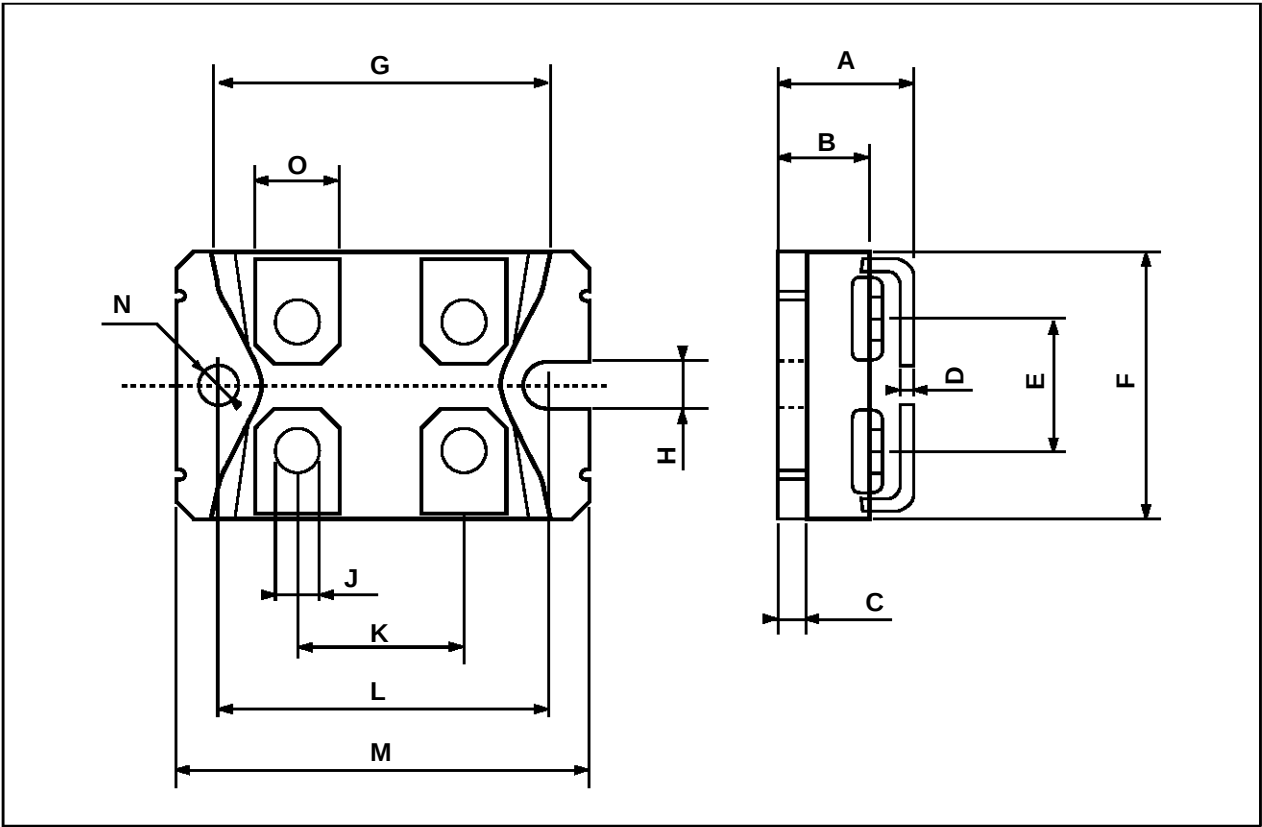
3) Fast recovery rectifier

Turn-off Switching Waveforms.



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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